



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re: U.S. Patent Application 10 001,429) PATENT
German Title: Schreib-Leseverstärker für eine DRAM-)
Speicherzelle sowie DRAM-Speicher)
English Translation: Read/write amplifier for a DRAM)
Memory cell, and DRAM memory)
Applicant: Infineon Technologies, AG)
Inventors: Alexander Frey)
Attorney Docket No: 32226.14)

RECEIVED

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Technology Center

Sir:

PRELIMINARY AMENDMENT

In the above-entitled patent application, please amend the application as follows:

In the Claims

1 1. (amended) A read/write amplifier for a DRAM memory cell, which, for
2 evaluation of the information content of at least one DRAM memory cell, is connected or can be
3 connected to at least one bit line and to at least one reference bit line, which in each case form a
4 bit line pair, having a number of components for assessment, amplification and forwarding of
5 voltage signals read from the bit lines and reference bit lines, in which case the read/write
6 amplifier has a first read/write amplifier element and a second read/write amplifier element
7 separate therefrom, and in that the individual amplifier components are divided between the two
8 read/write amplifier elements.